Technical Data
Data Sheet N1849, Rev. B

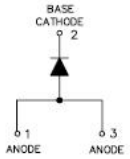
STD20200 SCHOTTKY RECTIFIER

DPAK

Features

- 150°C T_J operation
- Ultralow forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Trench MOS Schottky technology
- Terminals finish: Tin Lead-free plated
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	200	V
Average Rectified Forward Current	$I_{F(AV)}$	50% duty cycle @Tc=100°C, rectangular wave form	20	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3ms, Half Sine pulse	170	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop *	V_{F1}	@ 5A, Pulse, T_J = 25 °C @ 10A, Pulse, T_J = 25 °C @ 20A, Pulse, T_J = 25 °C	0.68 0.75 0.84	- - 1.10	V
	V_{F2}	@ 5A, Pulse, T_J = 125 °C @ 10A, Pulse, T_J = 125 °C @ 20A, Pulse, T_J = 125 °C	0.55 0.60 0.70	- - 0.72	V
Reverse Current*	I_{R1}	@V_R = rated V_R, T_J = 25 °C	0.001	0.2	mA
	I_{R2}	@V_R = rated V_R, T_J = 125 °C	1	12	mA
Junction Capacitance	C_T	@V_R = 5V, T_C = 25 °C f_{SIG} = 1MHz	400	-	pF

* Pulse width < 300 μs, duty cycle < 2%

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Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	°C
Storage Temperature	T_{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	2.2	°C/W
Approximate Weight	wt	-	0.39	g
Case Style	DPAK			

Ratings and Characteristics Curves

Figure1
Typical Forward Characteristics

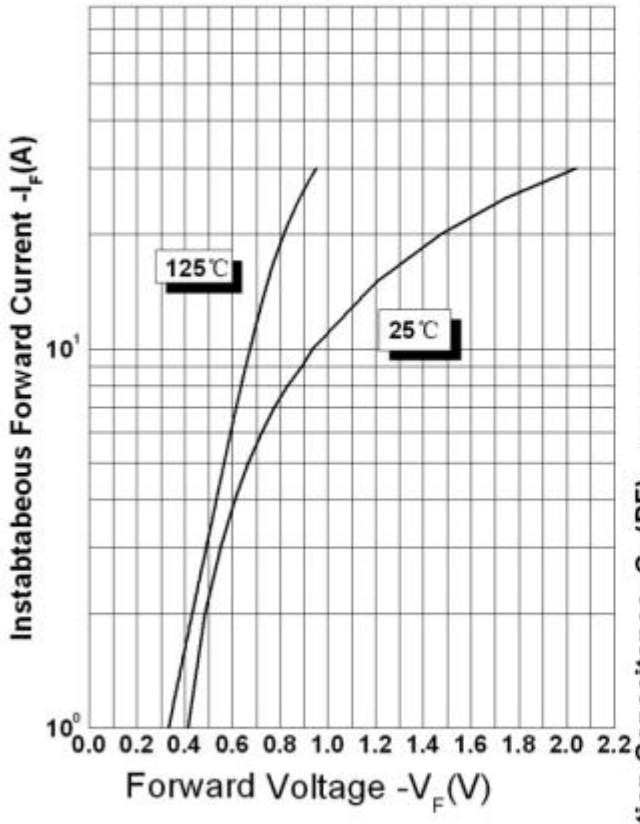


Figure 2
Typical Reverse Characteristics

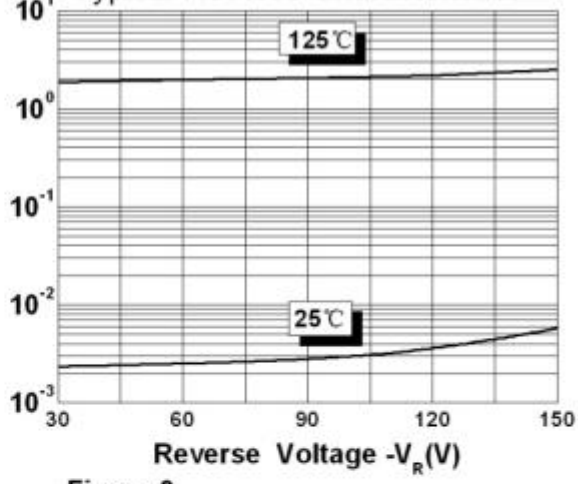
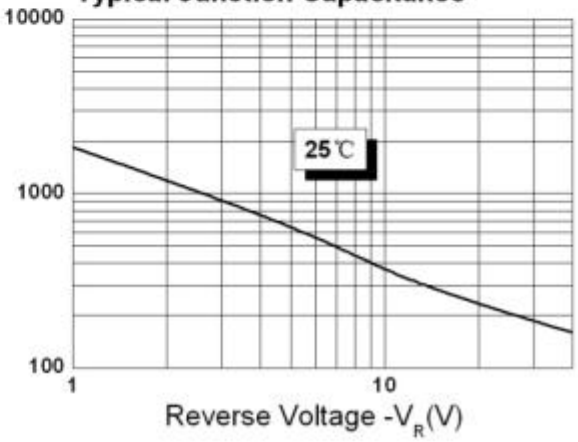


Figure 3
Typical Junction Capacitance



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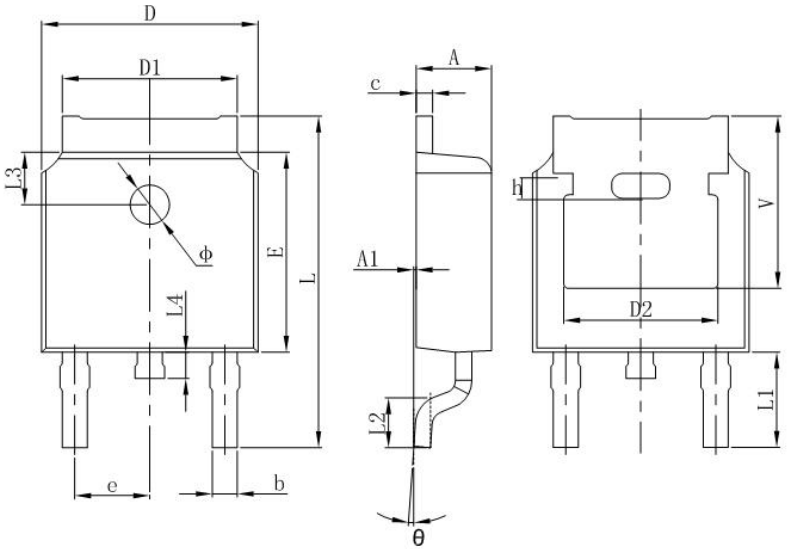
Mechanical Dimensions DPAK



The outline from different package houses may have slight differences. So the outline above is just schematic. The dimensions are controlled per specifications.

Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	2.18	-	2.39
A1	-	-	0.13
b	0.64	-	0.89
c	0.46	-	0.89
D	6.35	-	6.73
D1	4.95	-	5.46
D2	4.32	-	-
E	5.97	6.1	6.22
e		2.29BSC	
L	9.4	-	10.41
L1		2.90 REF.	
L2	1.4	1.52	1.78
L3		1.60 REF.	
L4	-	-	1.02
Φ	1.1	-	1.3
θ	0°	-	10°
V	5.21	-	-

Ordering Information

Device	Package	Shipping
STD20200	DPAK	2500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

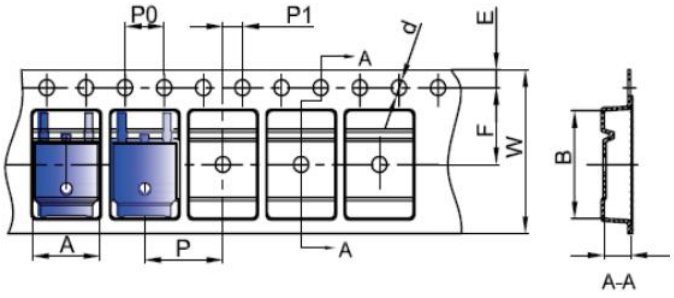
Marking Diagram

Where XXXXX is YYWWL

ST	= Device Type
D	= Package type
20	= Forward Current (20A)
200	= Reverse Voltage(200V)
SSG	= SSG
YY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Carrier Tape Specification DPAK



SYMBOL	Millimeters	
	Min.	Max.
A	6.80	7.00
B	10.40	10.60
C	2.60	2.80
d	Φ1.45	Φ1.65
E	1.65	1.85
F	7.40	7.60
P0	3.90	4.10
P	7.90	8.10
P1	1.90	2.10
W	15.90	16.30

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